

## 2 Port, USB 2.0 High Speed (480 Mbps) Switch, DPDT Analog Switch

### DESCRIPTION

The DG2720 is 2 Port high speed analog switch optimized for USB 2.0 signal switching. The DG2720 switch is configured in DPDT. It handles bidirectional signal flow, achieving a 620 MHz -3 dB bandwidth with 5 pF load, and a port to port Crosstalk and isolation at -49 dB.

Processed with high density sub micron CMOS, the DG2720 provide low parasitic capacitance. Signals are routed with minimized phase distortion and attain a bit to bit skew is as low as 40 pS.

The DG2720 is designed for a wide range of operating voltages, from 2.7 V to 4.3 V that can be driven directly from one cell Li-ion battery. On-chip circuitry protects against conditions when either the D+/D- lines are shorted to the  $V_{BUS}$  at the USB port. Additionally, logic control pins (S and  $\overline{OE}$ ) can tolerate the presence of voltages that are above the supply power rail ( $V_+$ ). The control logic threshold is guaranteed to be ( $V_{IH} = 1.3$  V/min).

Latch up current is greater than 300 mA, as per JESD78, and its ESD tolerance exceeds 8 kV.

Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free “-E4” suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL rating.

As a further sign of Vishay Siliconix's commitment, the DG2720 is fully RoHS compliant.

### FEATURES

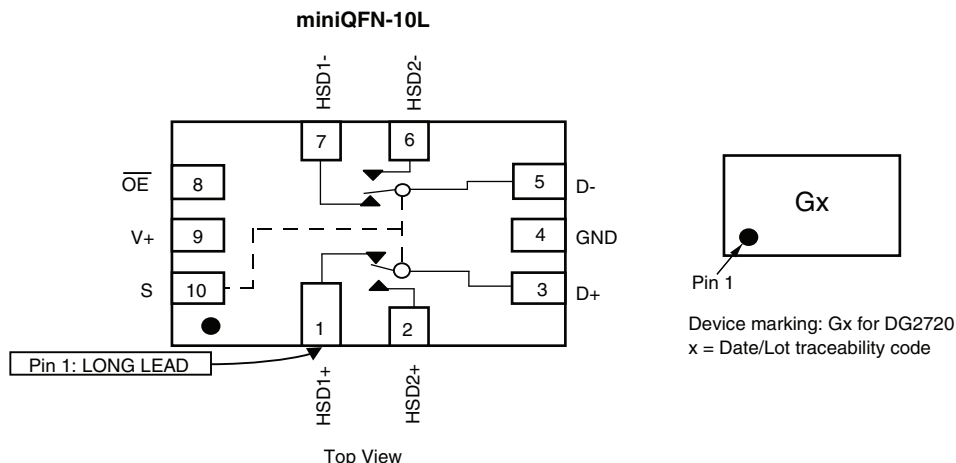
- Wide operation voltage range
- Low on-resistance, 5.7  $\Omega$  (typical at 3 V)
- Low capacitance, 5.6 pF (typical)
- 3 dB high bandwidth with 5 pF load: 620 MHz (typical)
- Low bit to bit skew: 40 pS (typical)
- Low power consumption
- Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5 V when  $V_+ = 0$  V
- Logic (S and  $\overline{OE}$ ) above  $V_+$  tolerance
- Latch-up current greater than 300 mA per JESD78
- 8 kV ESD protection (HBM)
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### APPLICATIONS

- Cellular phones
- Portable media players
- PDA
- Digital camera
- GPS
- Notebook computer
- TV, monitor, and set top box

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



**ORDERING INFORMATION**

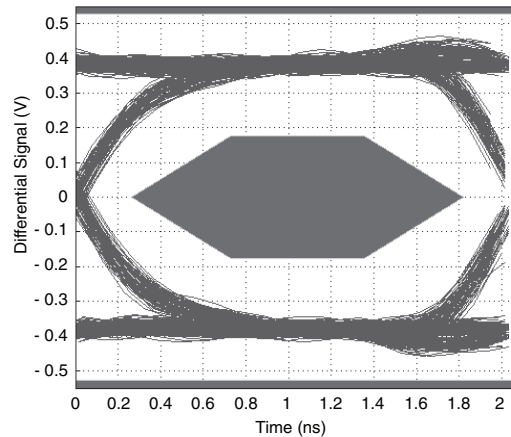
TEMP RANGE	PACKAGE	PART NUMBER
-40 °C to +85 °C	miniQFN-10	DG2720DN-T1-E4

**TRUTH TABLE**

$\overline{OE}$ (PIN 8)	S (PIN 10)	FUNCTION
0	0	D+ = HSD1+ and D- = HSD1-
0	1	D+ = HSD2+ and D- = HSD2-
1	X	Disconnect

**PIN DESCRIPTIONS**

PIN NAME	DESCRIPTION
$\overline{OE}$	Bus Switch Enable
S	Select Input
HSD1±, HSD2±, D±	Data Port


**High Speed Signal Quality Eye Diagram Test with V+ = 3.3 V**
**SUMMARY OF THE USB 2.0 SIGNAL QUALITY TEST RESULTS**

Compliance Test	High Speed
Signal Eye Test	Pass
EOP Width	7.95 bits
Measured Signal Rate	480.0009 MHz
Consecutive Jitter Range	-59.8 ps to 68.2 ps, RMS Jitter 26.8 ps
Paired JK Jitter Range	-49.7 ps to 51.4 ps, RMS Jitter 25.3 ps
Paired KJ Jitter Range	-61.3 ps to 58.5 ps, RMS Jitter 26.8 ps

**ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25\text{ °C}$ , unless otherwise noted)

PARAMETER		LIMIT	UNIT
Reference to GND	V+	-0.3 to +5	V
	S, $\overline{OE}$ , D±, HSD1±, HSD2± <sup>a</sup>	-0.3 to (V+ + 0.3)	
Current (Any Terminal except S, $\overline{OE}$ , D±, HSD1±, HSD2±)		30	mA
Continuous Current (S, $\overline{OE}$ , D±, HSD1±, HSD2±)		± 250	
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 500	
Storage Temperature (D Suffix)		-65 to +150	°C
Power Dissipation (Packages) <sup>b</sup>	miniQFN-10 <sup>c</sup>	208	mW
ESD (Human Body Model) I/O to GND		8	kV
Latch-up (Current Injection)		350	mA

**Notes**

- Signals on S,  $\overline{OE}$ , D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC board.
- Derate 2.6 mW/°C above 70 °C.



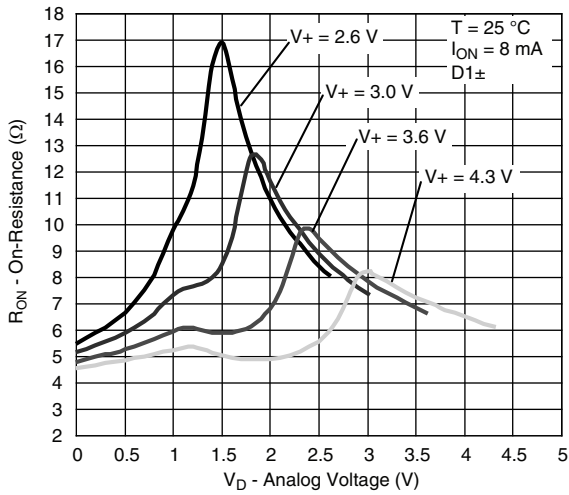
SPECIFICATIONS V+ = 3 V							
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED	TEMP. <sup>a</sup>	LIMITS -40 to +85 °C			UNIT
				MIN. <sup>b</sup>	TYP. <sup>c</sup>	MAX. <sup>b</sup>	
<b>Analog Switch</b>							
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>	R <sub>DS(on)</sub>	Full	0	-	V+	V
On-Resistance	R <sub>DS(on)</sub>	V+ = 3 V, I <sub>D±</sub> = 8 mA, V <sub>HSD1/2±</sub> = 0.4 V	Room	-	5.7	7	Ω
			Full	-	-	9	
On-Resistance Match <sup>d</sup>	ΔR <sub>ON</sub>	V+ = 3 V, I <sub>D±</sub> = 8 mA, V <sub>HSD1/2±</sub> = 0.4 V	Room	-	0.35	-	
On-Resistance Resistance Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	V+ = 3 V, I <sub>D±</sub> = 8 mA, V <sub>HSD1/2±</sub> = 0 V, 1 V	Room	-	2	-	
Switch Off Leakage Current	I <sub>(off)</sub>	V+ = 4.3 V, V <sub>HSD1/2±</sub> = 0.3 V, 3 V, V <sub>D±</sub> = 3 V, 0.3 V	Full	-100	-	100	nA
Channel On Leakage Current	I <sub>(on)</sub>	V+ = 4.3 V, V <sub>HSD1/2±</sub> = 0.3 V, 4 V, V <sub>D±</sub> = 4 V, 0.3 V	Full	-200	-	200	
<b>Digital Control</b>							
Input Voltage High	V <sub>INH</sub>	V+ = 3 V to 3.6 V	Full	1.3	-	-	V
		V+ = 4.3 V	Full	1.7	-	-	
Input Voltage Low	V <sub>INL</sub>	V+ = 3 V to 4.3 V	Full	-	-	0.5	
Input Capacitance	C <sub>IN</sub>		Full	-	5.6	-	pF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	-1	-	1	μA
<b>Dynamic Characteristics</b>							
Break-Before-Make Time <sup>e, d</sup>	t <sub>BBM</sub>	V+ = 3 V, V <sub>D1/2±</sub> = 1.5 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 35 pF	Room	-	5	-	ns
			Full	-	5	-	
Enable Turn-On Time <sup>e, d</sup>	t <sub>ON(EN)</sub>	V+ = 3 V, V <sub>D1/2±</sub> = 1.5 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 35 pF	Room	-	-	30	ns
			Full	-	-	30	
Enable Turn-Off Time <sup>e, d</sup>	t <sub>OFF(EN)</sub>	V+ = 3 V, V <sub>D1/2±</sub> = 1.5 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 35 pF	Room	-	-	25	ns
			Full	-	-	25	
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, R <sub>GEN</sub> = 0 Ω, V <sub>GEN</sub> = 0 V	Room	-	0.5	-	pC
Off-Isolation <sup>d</sup>	OIRR	V+ = 3 V to 3.6 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 240 MHz		-	-30	-	dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>			-	-49	-	
Bandwidth <sup>d</sup>	BW	V+ = 3 V to 3.6 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, -3 dB	Room	-	620	-	MHz
Channel-Off Capacitance <sup>d</sup>	C <sub>D1±(off)</sub>	V+ = 3.3 V, f = 1 MHz		-	4	-	pF
	C <sub>D2±(off)</sub>			-	4	-	
Channel-On Capacitance <sup>d</sup>	C <sub>D±(off)</sub>			-	5.6	-	
	C <sub>D±(on)</sub>			-	11	-	
Channel-to-Channel Skew <sup>d</sup>	t <sub>SK(O)</sub>			-	50	-	
Skew Off Opposite Transitions of the Same Output <sup>d</sup>	t <sub>SK(p)</sub>	V+ = 3 V to 3.6 V, R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	-	20	-		
Total Jitter <sup>d</sup>	t <sub>J</sub>		-	200	-		
<b>Power Supply</b>							
Power Supply Range	V+			2.6	-	4.3	V
Power Supply Current	I+	V <sub>IN</sub> = 0 V, or V+	Full	-	-	2	μA

**Notes**

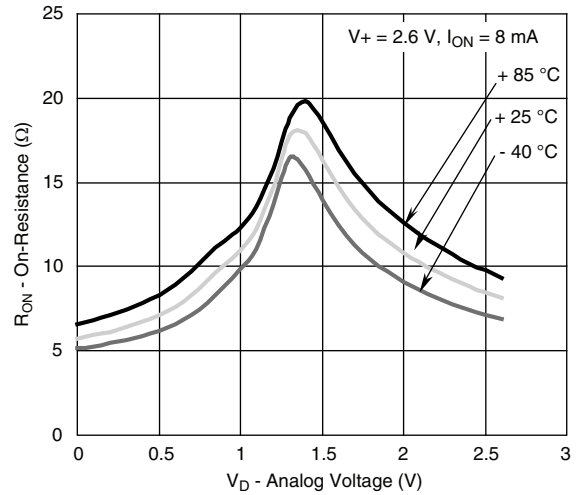
- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e. V<sub>IN</sub> = input voltage to perform proper function.
- f. Crosstalk measured between channels

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

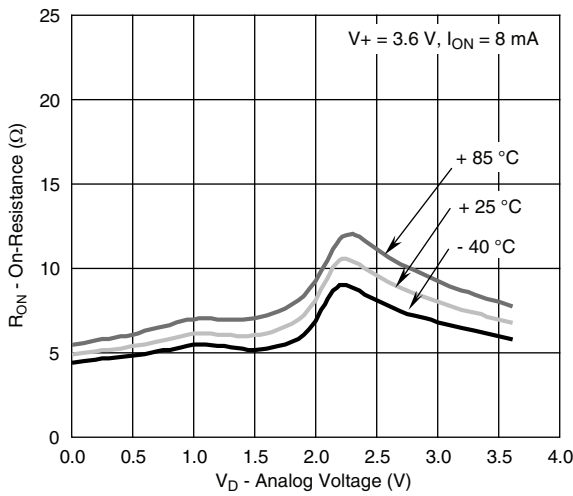
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



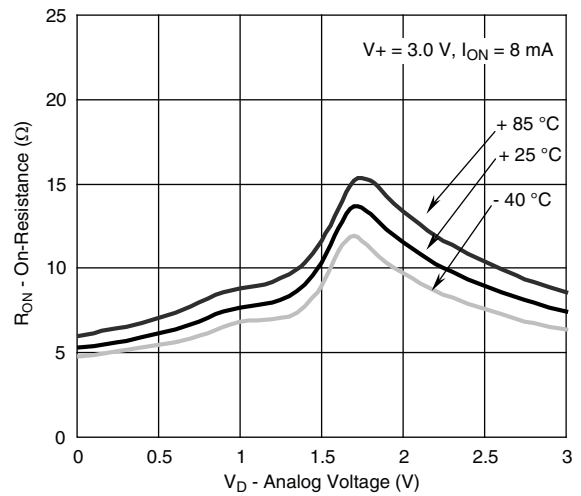
**On-Resistance vs.  $V_D$  and Single Supply Voltage**



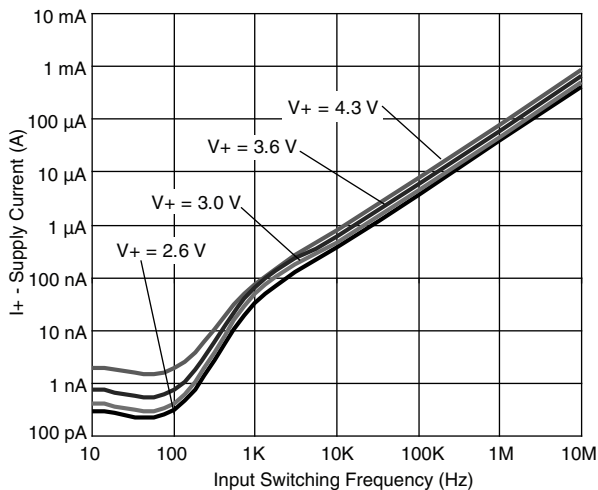
**On-Resistance vs. Analog Voltage and Temperature**



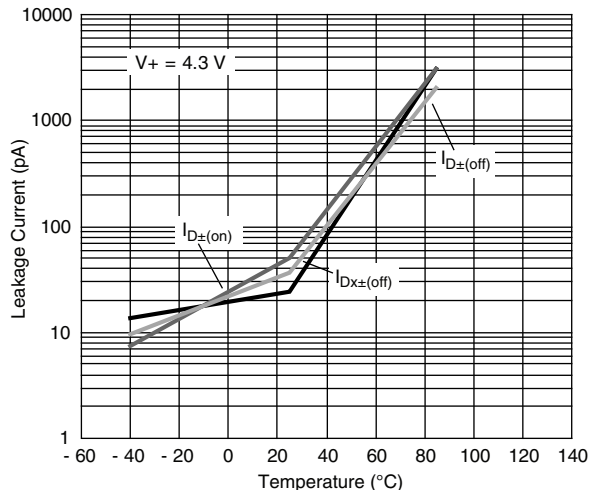
**On-Resistance vs. Analog Voltage and Temperature**



**On-Resistance vs. Analog Voltage and Temperature**

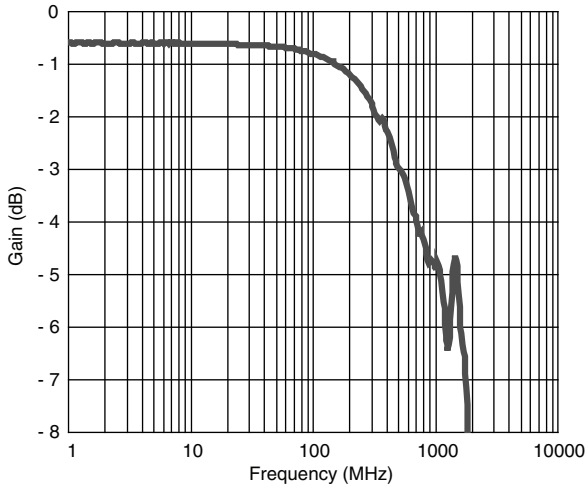


**Supply Current vs. Input Switching Frequency**

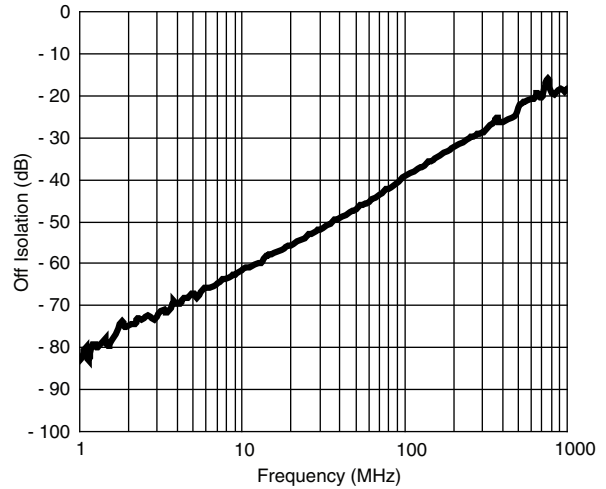


**Leakage Current vs. Temperature**

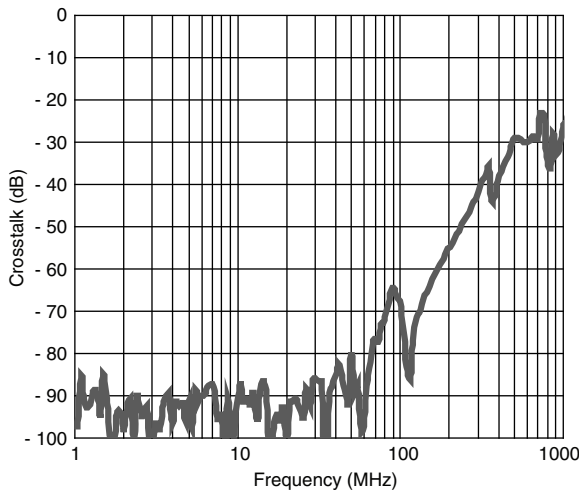
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Gain vs. Frequency,  $C_L = 5\text{ pF}$ ,  $V_+ = 3.3\text{ V}$**

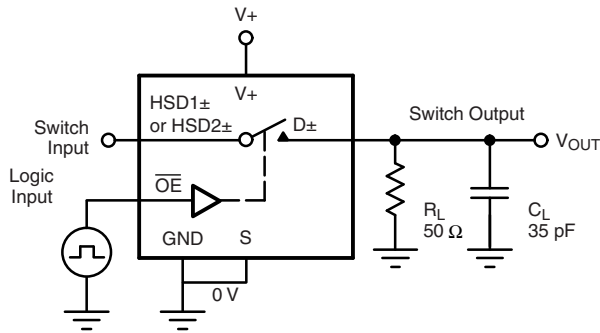


**OFF Isolation,  $V_+ = 3.3\text{ V}$**



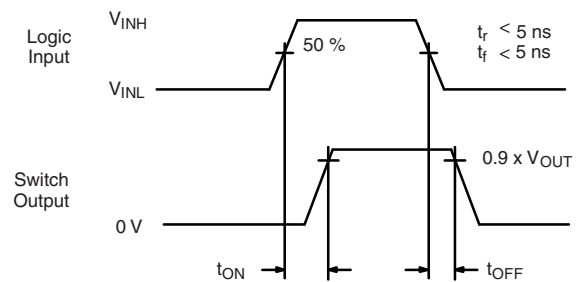
**Crosstalk,  $V_+ = 3.3\text{ V}$**

**TEST CIRCUITS**



$C_L$  (includes fixture and stray capacitance)

$$V_{OUT} = D_{\pm} \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On  
Logic input waveforms inverted for switches that have the opposite logic sense.

**Fig. 1 - Switching Time**

TEST CIRCUITS

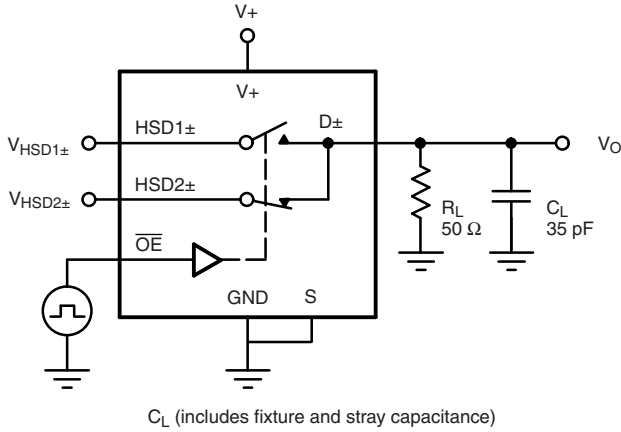
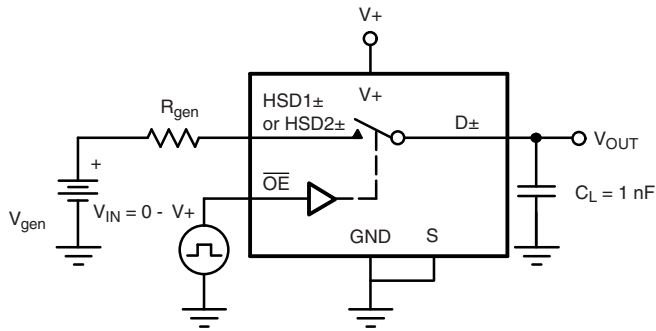


Fig. 2 - Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection

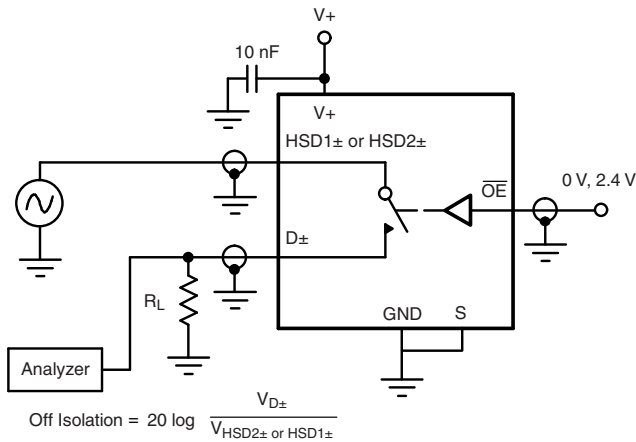


Fig. 4 - Off-Isolation

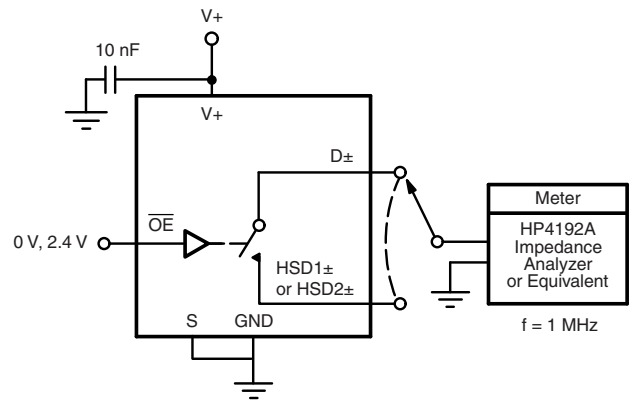
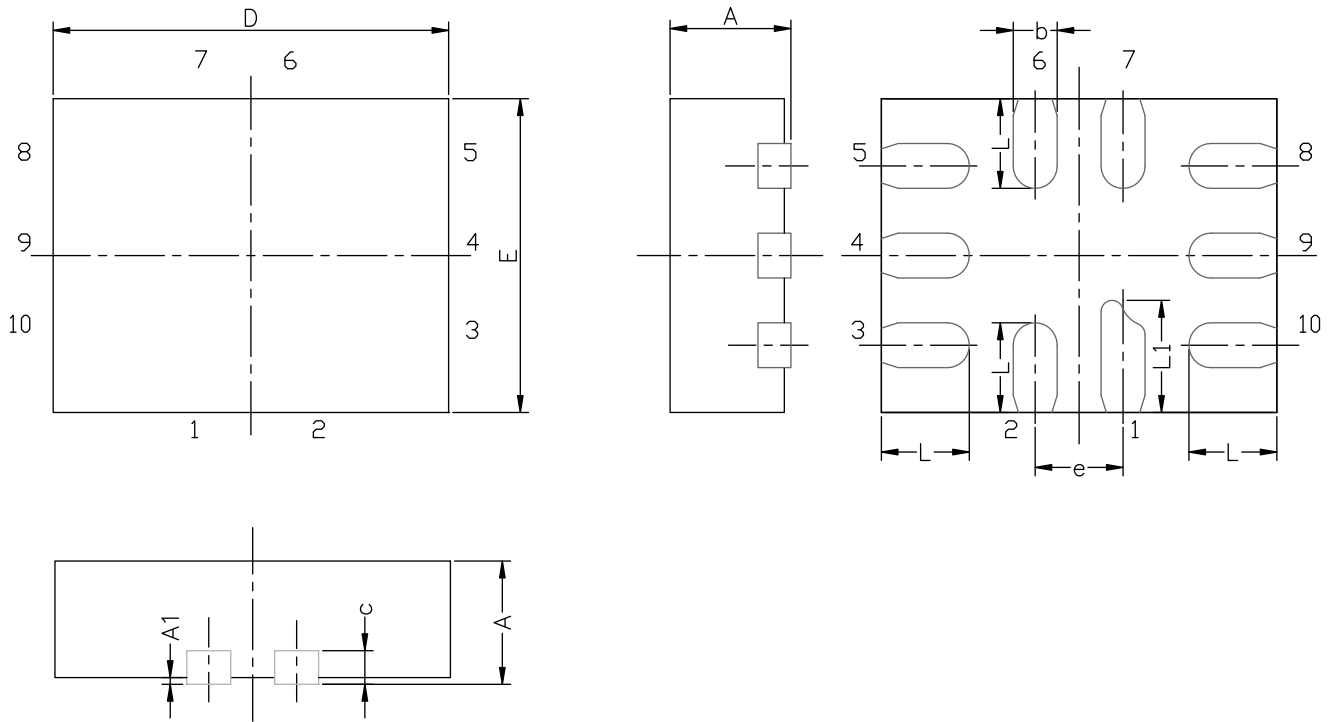


Fig. 5 - Channel Off/On Capacitance

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### MINI QFN-10L CASE OUTLINE



DIM	MILLIMETERS			INCHES		
	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.
A	0.45	0.55	0.60	0.0177	0.0217	0.0236
A1	0.00	-	0.05	0.000	-	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.150 or 0.127 REF <sup>(1)</sup>			0.006 or 0.005 REF <sup>(1)</sup>		
D	1.70	1.80	1.90	0.067	0.071	0.075
E	1.30	1.40	1.50	0.051	0.055	0.059
e	0.40 BSC			0.016 BSC		
L	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217

**Note**

<sup>(1)</sup> The dimension depends on the leadframe that assembly house used.

ECN T16-0163-Rev. B, 16-May-16  
DWG: 5957

**RECOMMENDED MINIMUM PADS FOR MINI QFN 10L**



Mounting Footprint  
Dimensions in mm (inch)





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